

**Amendments to the Claims:**

This listing of claims will replace all prior versions, and listings, of claims, including those in the First Preliminary Amendment, in the application:

**Listing of Claims:**

Claim 1 (original - Article 19): A Ge-Cr alloy sputtering target containing 5 to 50at% of Cr characterizing in that said target has a relative density of 97% or more, that the density variation of said target is within  $\pm 1.5\%$ , and that, in X-ray diffraction, the ratio B/A of the maximum peak intensity A of Ge phase in a  $2\theta$  range of  $20^\circ$  to  $30^\circ$  and of the maximum peak intensity B of GeCr compound phase in a  $2\theta$  range of  $30^\circ$  to  $40^\circ$  is 0.18 or more.

Claims 2-3 (canceled).

Claim 4 (original - Article 19): Ge-Cr alloy sputtering target according to claim 1, wherein the composition variation in the target is within  $\pm 0.5\%$ .

Claim 5 (canceled).

Claim 6 (currently amended): A manufacturing method of a Ge-Cr alloy sputtering target, comprising the steps of evenly dispersing and mixing Cr powder of  $75\mu\text{m}$  or less, and Ge powder of  $250\mu\text{m}$  or less and having a BET specific surface area of 0.1 to  $0.4\text{m}^2/\text{g}$  ~~or less~~, and thereafter performing sintering thereto.

Claims 7-9 (canceled).

Claim 10 (new): A method according to claim 6, wherein sintering is performed under the conditions of hot pressing at a sintering temperature of 760 to 900°C and a surface pressure of 75 to 250kg/cm<sup>2</sup>.

Claim 11 (new): A method of manufacturing a Ge-Cr alloy sputtering target, comprising the steps of evenly dispersing and mixing Cr powder of 75μm or less, and Ge powder of 250μm or less having a BET specific surface area of 0.1 to 0.4m<sup>2</sup>/g, and thereafter performing sintering thereto, wherein said sputtering target formed by the method contains 5 to 50at% of Cr, has a relative density of 97% or more and a density variation within ±1.5%, and has in X-ray diffraction a ratio B/A of a maximum peak intensity A of Ge phase in a 2θ range of 20° to 30° and of a maximum peak intensity B of GeCr compound phase in a 2θ range of 30° to 40°, said ratio B/A being 0.18 or more.

Claim 12 (new): A method according to claim 11, wherein sintering is performed under the conditions of hot pressing at a sintering temperature of 760 to 900°C and a surface pressure of 75 to 250kg/cm<sup>2</sup>.

Claim 13 (new): A method according to claim 12, wherein a composition variation in the target is within ±0.5%.

Claim 14 (new): A method according to claim 11, wherein a composition variation in the target is within ±0.5%.